

IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



BTA410X-800BT

3Q Hi-Com Triac

28 May 2014

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This "series BT" triac will commute the full RMS current at the maximum rated junction temperature ($T_{j(max)} = 150\text{ }^{\circ}\text{C}$) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction operating temperature capability
- High voltage capability
- Isolated mounting base package
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

3. Applications

- Applications subject to high temperature
- Industrial and domestic heating circuits
- Motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

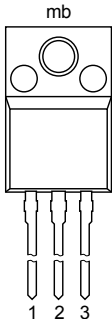
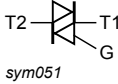
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	100	A
T_j	junction temperature		-	-	150	$^{\circ}\text{C}$
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 98\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	10	A



Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7		2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7		2	-	50	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7		2	-	50	mA
Dynamic characteristics							
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 150 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit		1000	-	-	V/μs
dI _{com} /dt	rate of change of commutating current	V _D = 400 V; T _j = 150 °C; I _{T(RMS)} = 10 A; dV _{com} /dt = 20 V/μs; (snubberless condition); gate open circuit		20	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 TO-220F (SOT186A)	 sym051
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA410X-800BT	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_h \leq 98^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	10	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	100	A
		full sine wave; $T_{\text{j(init)}} = 25^\circ\text{C}$; $t_p = 16.7\text{ ms}$	-	110	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	50	A^2s
dl_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 20\text{ A}$; $I_{\text{G}} = 0.2\text{ A}$; $dl_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^\circ\text{C}$
T_{j}	junction temperature		-	150	$^\circ\text{C}$

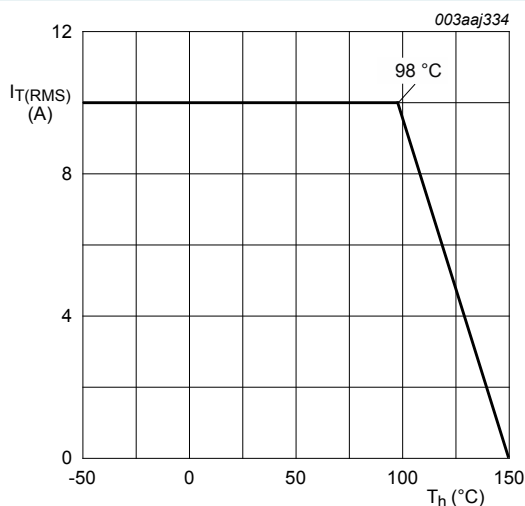
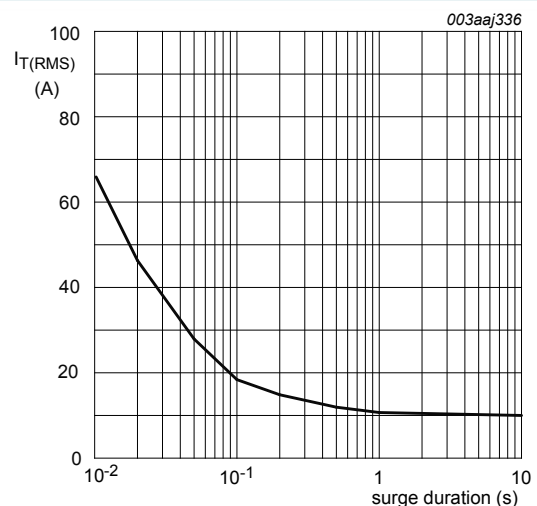


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



$f = 50\text{ Hz}$; $T_h = 98^\circ\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

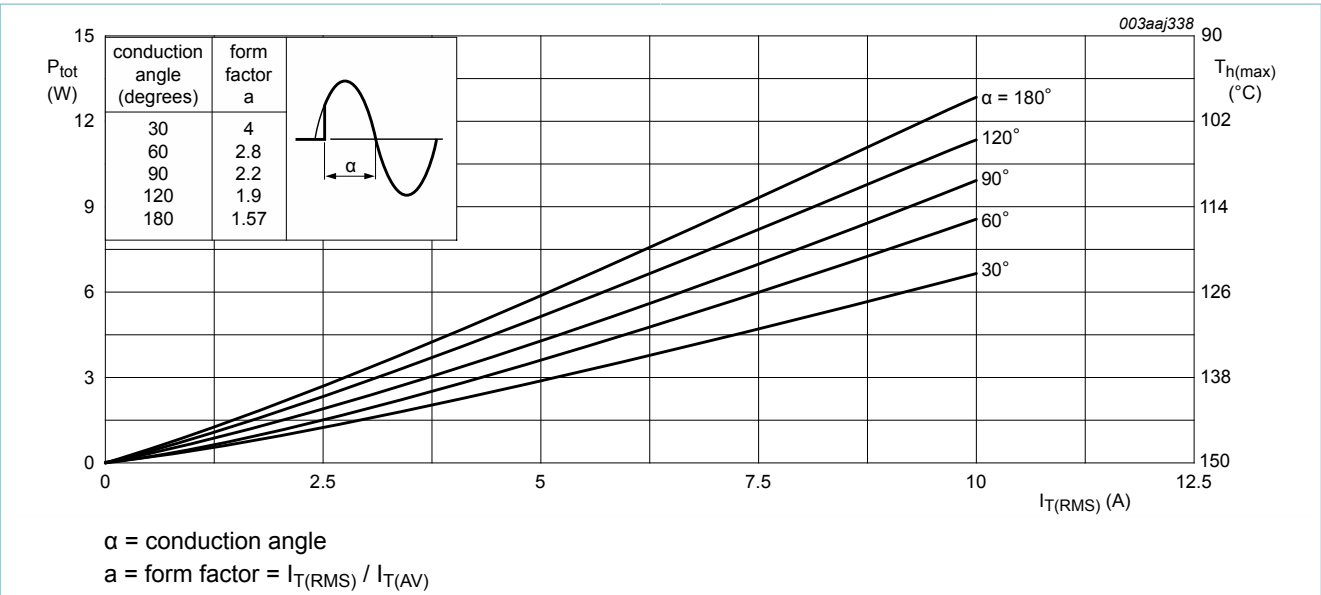


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

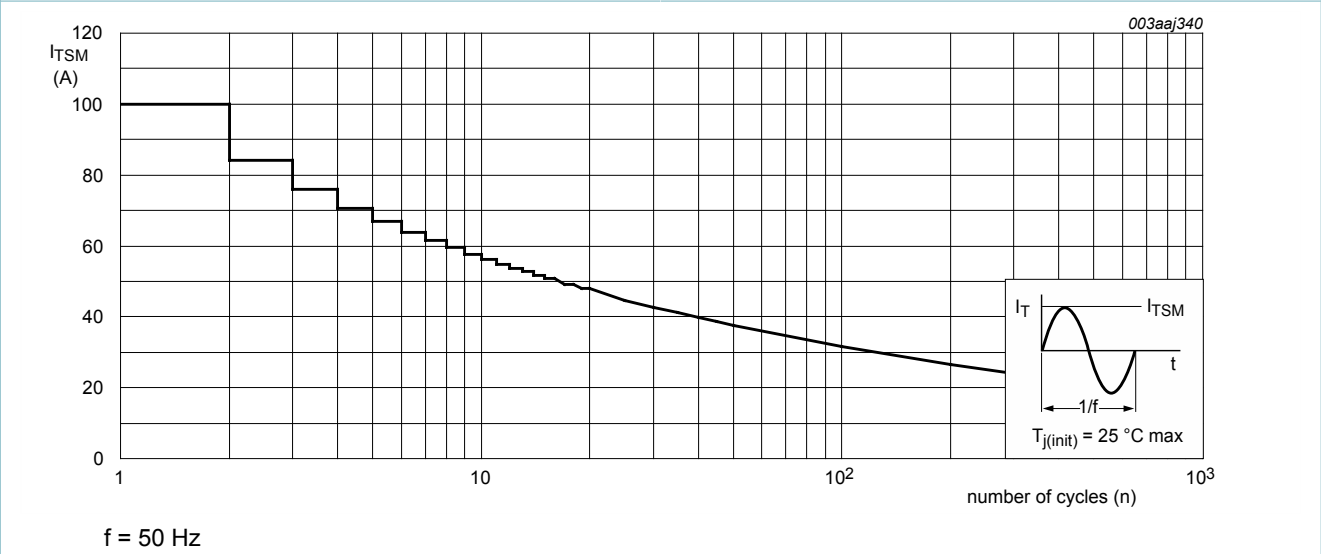
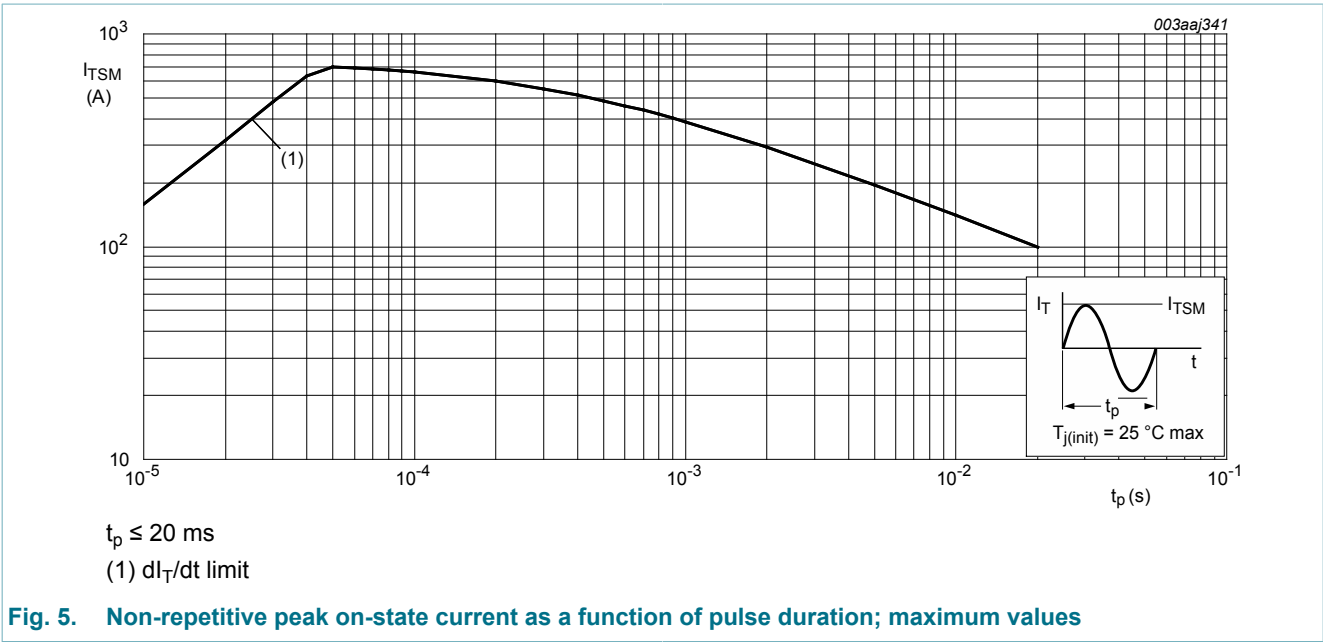


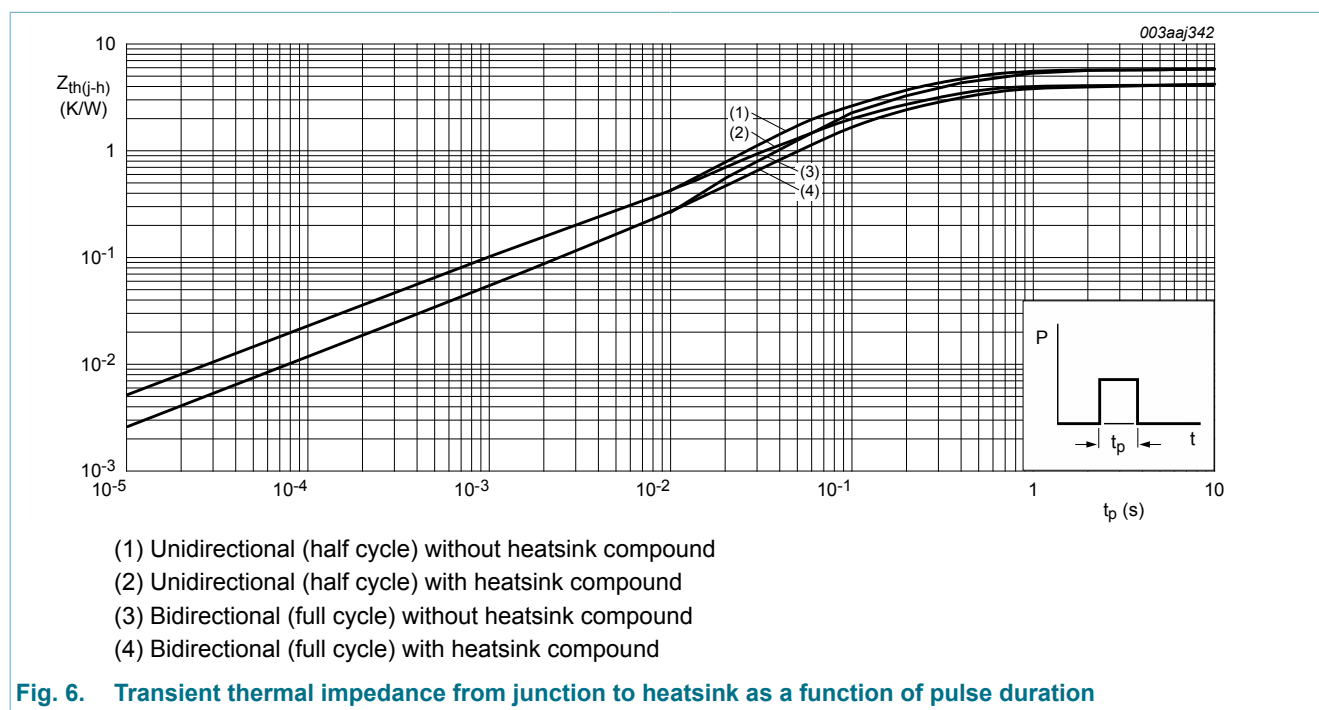
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; Fig. 6	-	-	4	K/W
		full cycle or half cycle; without heatsink compound; Fig. 6	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



9. Isolation characteristics

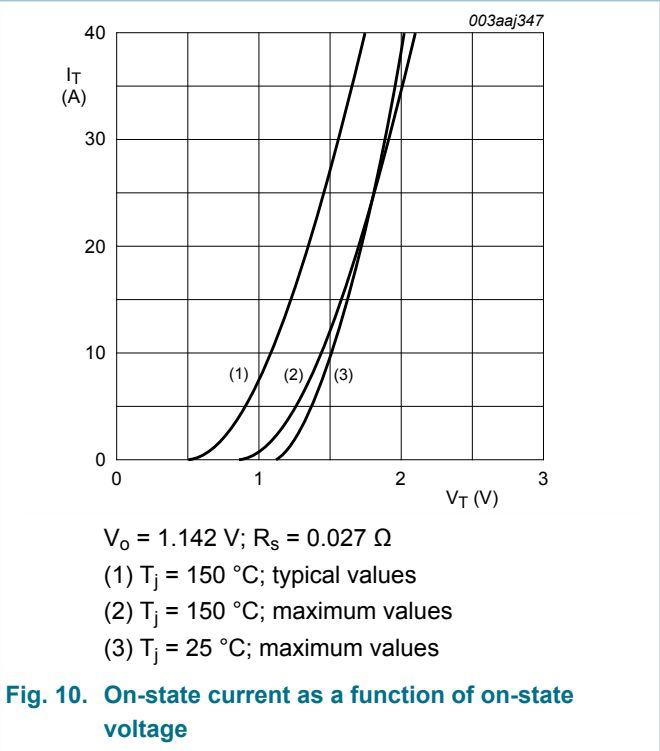
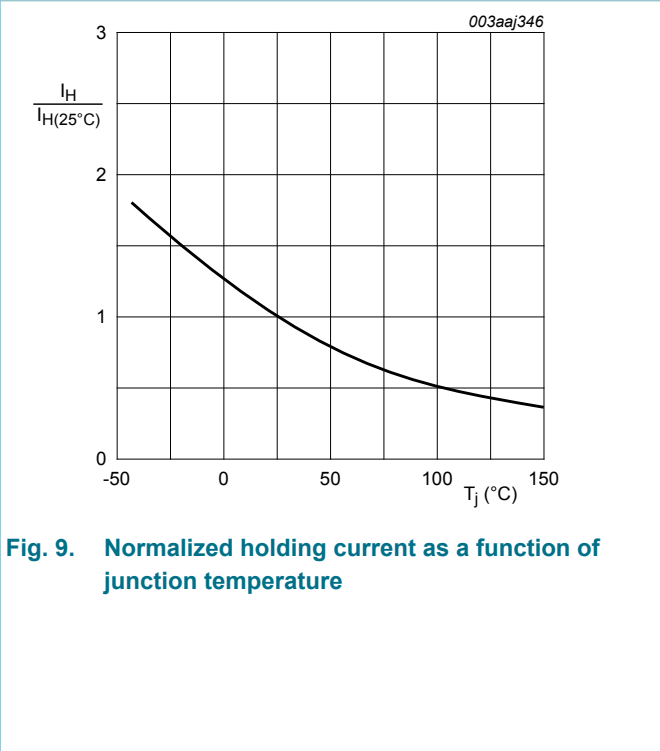
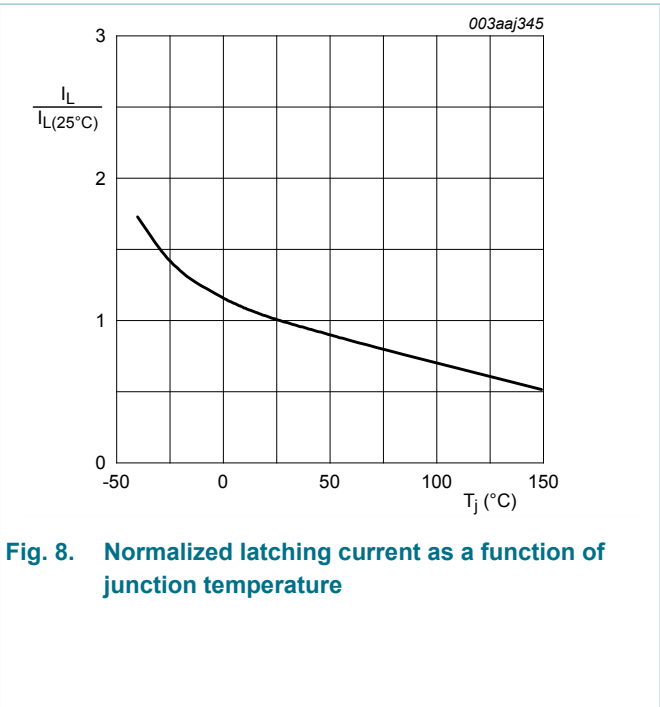
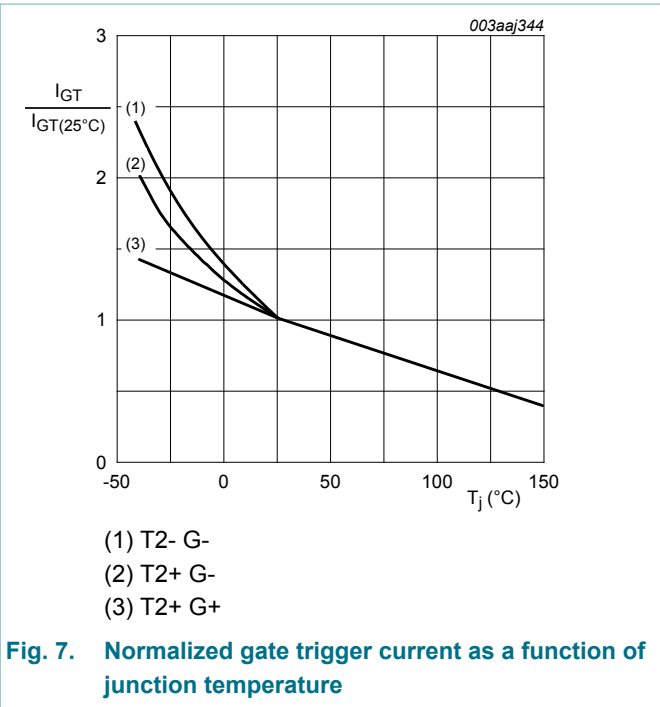
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$; $RH \leq 65\%$; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
C_{isol}	isolation capacitance	from main terminal 2 to external heatsink; $f = 1\text{ MHz}$; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	2	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	2	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	2	-	50	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	60	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	90	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	60	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	-	60	mA
V_T	on-state voltage	$I_T = 15\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	0.8	1	V
		$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; Fig. 11	0.25	0.4	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$	-	0.4	2	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 10\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit	20	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 10\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	28	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 150\text{ }^\circ\text{C}$; $I_{T(RMS)} = 10\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	45	-	-	A/ms



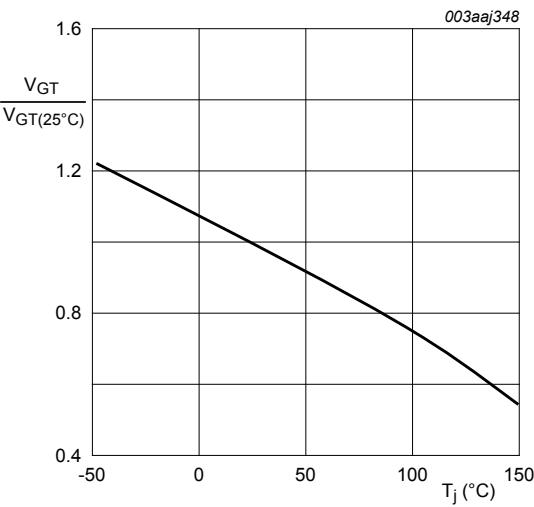


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

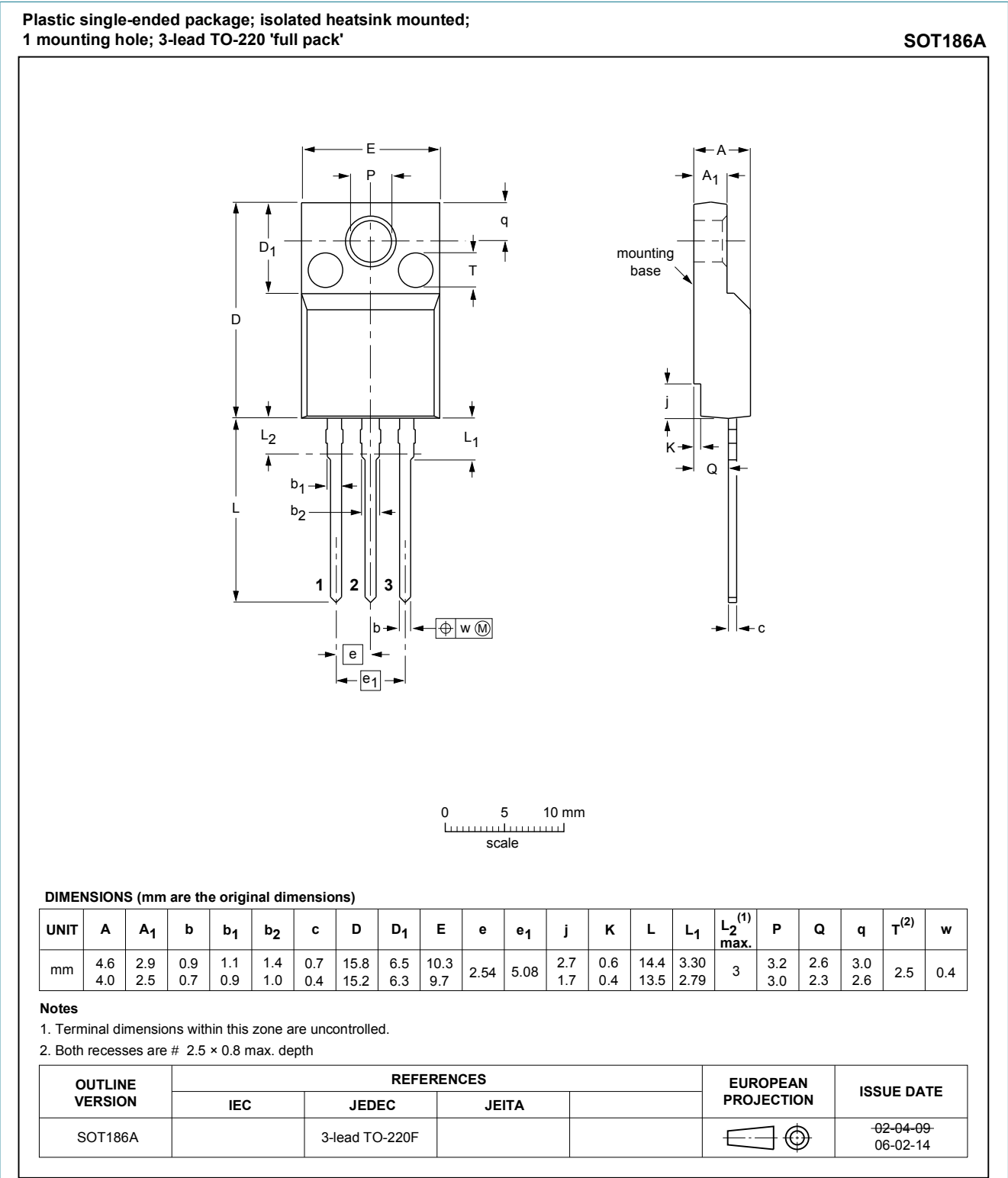


Fig. 12. Package outline TO-220F (SOT186A)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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